

MICRO ELECTRONICS

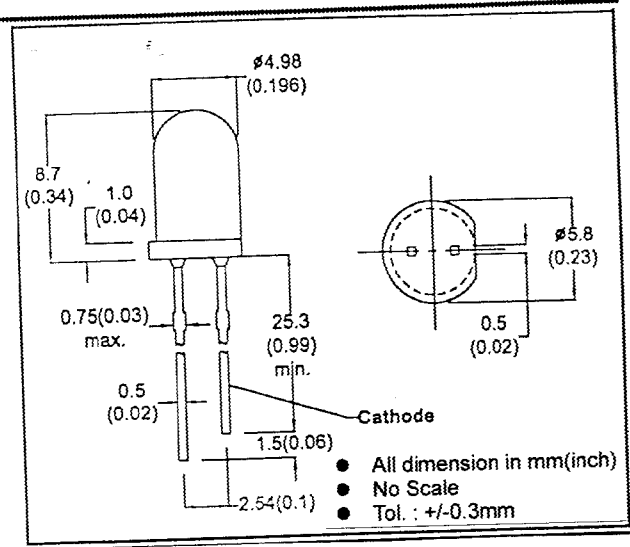
MIB57T-K

INFRARED
EMITTING
DIODE

DESCRIPTION

MIB57T-K is a GaAlAs infrared emitting diode molded in clear plastic 5mm diameter package. With the lensing effect of the package.

MIB57T-K is spectrally matched to the PIN photo diode ML303.



ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	150mW
Operating Temperature Range	-40 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C

* Pulse Width = 10 μ s, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTI (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	2.62	4.5		mW	IF=20mA
Forward Voltage	VF		1.2	1.6	V	IF=100mA
Reverse Current	IR			10	μ A	VR=5V
Peak Wavelength	λ_p		940		nm	IF=20mA
Spectrum Line Half Width	$\Delta\lambda$		45		nm	IF=20mA



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